Lattice location of implanted ⁶He in diamond

U. Wahl¹, J.G. Correia¹, A.R.G. Costa¹, B. Biesmans², G. Magchiels², S.M. Tunhuma², A. Vantomme², and L.M.C. Pereira²

1 Centro de Ciências e Tecnologias Nucleares, Instituto Superior Técnico, Universidade de Lisboa, Portugal

2 KU Leuven, Quantum Solid State Physics, Leuven, Belgium











- Fraction of ⁶He on T sites stable up to 600°C. then showing a 20% drop at 800°C.
- Possible reason for the drop: 6He starts to diffuse interstitially and is able to reach the surface of the sample or disappear into the bulk
- Under these assumptions, we can estimate the activation energy for interstitial migration of ⁶He as follows to be $E_{\rm M}$ =1.73 eV:

 $D = D_0 \exp \left[-\frac{E_M}{kT}\right]$ The diffusivity D of He is given by $D_0 = l^2 v_0 N_{\rm NN}$ *l*... interstitial jump width, v_0 ... jump attempt frequency With the entropy constant D_0

The mean diffusion width R is given by $R = \sqrt{D\tau}$ Taking the mean diffusion width R equal to the implantation depth R=1375 Å, we solve for E_{M}

Nww... number of available jump sites τ... radioactive lifetime of ⁶He

$E_{\rm M} = -kT \ln \left| \frac{D_0 \tau}{R^2} \right| = -kT \ln \left[\frac{l^2 \nu_0 N_{\rm NN} \tau}{R^2} \right]$

With τ =1.164 s, /=1.545 Å, $N_{\rm NN}$ =4, v_0 =2.39×10¹³ s⁻¹[6], T=1073 K, this yields $E_{\rm M}$ =1.73 eV.

800°C 92% T site T;=800°C (e) <110> (a) 9. (n (100)12 (f) <211> 1.0 (b) .075 (110) 0.0 -0.5 -1.0 (g) <100> (c) 1.0 0.5 (110) 0.0 1.085 1.024 0.964 -1.0 (h) <111> (d) 1.0 0.5 (110) 0.0 .108 .089 .069 -0.5 -1.0 -0.5 0.0 0.5 1.0 -1.0 -0.5 0.0 0.5 1.0 angle relative to axis [°] -1.0 normali

- General features of angular emission patterns: channeling along <100> and <111> axes, (100), (110) and (211) planes, blocking along <110> and <211> axes, (111) and (311) planes
- These features are consistent with occupation of tetrahedral interstitial T sites.
- Detailed analysis by means of fitting theoretical patterns gives the following results:
- T_i =RT=30°C: 108% T sites
- T₁ = 600°C: 111% T sites
- T =800°C: 92% T sites
- · No other sites could be identified
- Fitted fraction values above 100% indicate an inaccurate attribution of gamma and electron backscattering background. Estimated systematic error: +10% (constant for all measurements, thus does not explain changes with temperature).

Conclusions

β⁻ yield

- The vast majority (if not all) of implanted He in diamond is found on tetrahedral interstitial T sites in accordance with theoretical predictions [5-8]. Possible other lattice sites could not be identified and must be at maximum a few percent only.
- The activation energy $E_{\rm M}$ for interstitial migration of He in diamond suggested from our study is 1.73 eV, which is in reasonable agreement with theoretical predictions of E_M=2.35 eV [5], 1.97 eV [6], and 1.41 eV [9].
- Activation energies around 2 eV result in such high interstitial diffusivities (>6×10⁻¹¹ cm²s⁻¹) at earth mantle temperatures (~900-1400°C) that simple interstitial He in diamond cannot be stable on geological time scales of 109 years. The high pressure inside the mantle (up to 20 GPa) is suggested to lower $E_{\rm M}$ to 1.2 eV [9], so that diffusivities supposedly may even be considerably higher.
- To remain inside the diamond, He must be bound to defects in the material or exist in another form such as within inclusions of other minerals or liquids [2], possibly small He bubbles [9] or platelets [12].
- · These experiments are part of a systematic, wider study which also investigates other noble gas isotopes like ²³Ne (37 s), ⁸⁷Kr (76 min), ¹³³Xe (5.2 d), ¹³⁵Xe (9.1 h).

[12] W. Lin, et al, "Creating two-dimensional solid helium via diamond lattice confinement", Nature Comm. 13 (2022) 5990.





rs (FWO Portuguese Foundation for Science and Technology (FCT, CERN/FIS-TEC/0003/2021, UID/Multi/04349/2019) EU Horizon Europe Framework supported ISOLDE beam times through grant agreement 101057511 (EURO-LABS)



